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APPLICANT

Krishnaswamy RAMKUMAR, et al.

LIST OF REFERENCES CITED BY  
APPLICANT  
(Use Several Sheets if Necessary)

FILING DATE

October 12, 2001

GROUP ART UNIT

2812

## U.S. PATENT DOCUMENTS

| EXAMINER<br>INITIAL |    | DOCUMENT<br>NUMBER | DATE    | NAME         | CLASS | SUB<br>CLASS | FILING DATE IF<br>APPROPRIATE |
|---------------------|----|--------------------|---------|--------------|-------|--------------|-------------------------------|
| <i>Dkt</i>          | AA | 5,403,786          | 8/4/95  | Hori         | /     | /            |                               |
| <i>↓</i>            | AB | 5,521,127          | 5/28/96 | Hori         | /     | /            |                               |
| <i>↓</i>            | AC | 5,629,221          | 5/13/97 | Chao, et al. | /     | /            |                               |
| <i>Dkt</i>          | AD | 5,880,040          | 3/9/99  | Sun, et al.  | /     | /            |                               |
|                     | AE |                    |         |              |       |              |                               |
|                     | AF |                    |         |              |       |              |                               |

## FOREIGN PATENT DOCUMENTS

|  |    | DOCUMENT<br>NUMBER | DATE | COUNTRY | TRANSLATION<br>YES NO |
|--|----|--------------------|------|---------|-----------------------|
|  | AG |                    |      |         |                       |
|  | AH |                    |      |         |                       |

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

|            |    |  |
|------------|----|--|
| <i>Dkt</i> | AI | Gusev, et al., "Growth and Characterization of Ultrathin Nitrided Silicon Oxide Films", IBM J. Res. Develop., 43, 3, 265-286 (1999).                           |
| <i>↓</i>   | AJ | Hook, et al., "Nitrided Gate Oxides for 3.3-V Logic Application: Reliability and Device Design Considerations", IBM J. Res. Develop., 43, 3, 393-406 (1999).   |
| <i>↓</i>   | AK | Buchanan, "Scaling the Gate Dielectric: Materials Integration, and Reliability", IBM J. Res. Develop., 43, 3, 245-264 (1999).                                  |
| <i>Dkt</i> | AL | Evans, et al., "High Performance CMOS Devices with 20 Å Engineered Oxynitrided Gate Dielectrics", paper presented at Semicon Korea Technical Symposium (2000). |
|            | AM |  |
|            | AN |  |

EXAMINER

DATE CONSIDERED 1-13-03

\*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.